

SEMiX[®] 5

Bridge Rectifier Module (halfcontrolled)

SEMiX245DH16

Features

- Terminal height 17 mm
- Solderless assembling solution with PressFIT signal pins and screw power terminals
- NTC temperature sensor inside

Typical Applications*

- Input Bridge Rectifier for AC/DC motor control
- Power supply

Remarks

- Reliability tests performed at T_i = 130°C
- For storage and case temperature with TIM see document "TP(HALA P8) SEMiX 5p"

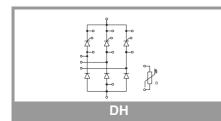
Absolute Maximum Ratings							
Symbol	Conditions		Values	Unit			
Module							
I _D	T _i = 130 °C	$T_c = 96 \ ^{\circ}C$ $T_c = 80 \ ^{\circ}C$	336	А			
	rec. 120°	T _c = 80 °C	440	А			
T _{stg}	module without TIM		-40 125	°C			
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V			

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit				
Thyristor								
I _{T(AV)}	T _i = 130 °C	T _c = 80 °C	154	А				
	sinus 180°	T _c = 100 °C	107	Α				
I _{TSM}	10	T _j = 25 °C	2050	А				
	_ 10 ms	T _j = 130 °C	1800	Α				
i ² t	10 ms	T _j = 25 °C	21013	A ² s				
		T _j = 130 °C	16200	A ² s				
V _{RSM}			1700	V				
V _{RRM}			1600	V				
V _{DRM}			1600	V				
(di/dt) _{cr}	T _j = 130 °C		100	A/µs				
(dv/dt) _{cr}	T _j = 130 °C		1000	V/µs				
Tj			-40 130	°C				

Absolute	Maximum Rati	ngs		
Symbol	Conditions		Values	Unit
Diode				
I _{FAV}	T _j = 150 °C	T _c = 80 °C	167	А
	sin. 180°	T _c = 100 °C	135	А
I _{FSM}	10 ms	T _j = 25 °C	2100	Α
		T _j = 130 °C	1700	А
i²t	- 10 ms	T _j = 25 °C	22050	A ² s
		T _j = 130 °C	14450	A ² s
V _{RSM}			1700	V
V _{RRM}			1600	V
Ti			-40 150	°C

Characteristics							
Symbol	Conditions min. typ. r				Unit		
Temperature Sensor							
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)	493 ± 5%			Ω		
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];	3550 ±2%		к			





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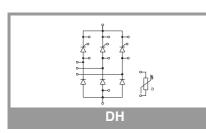
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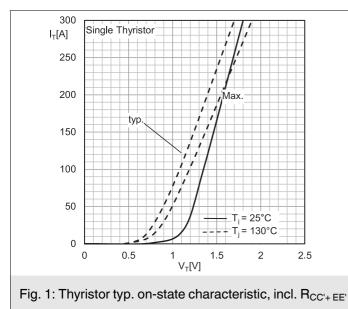
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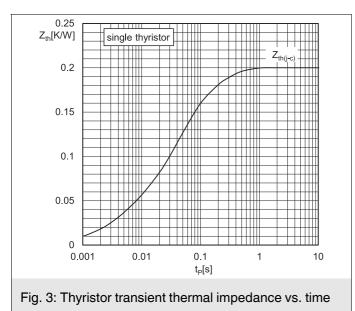


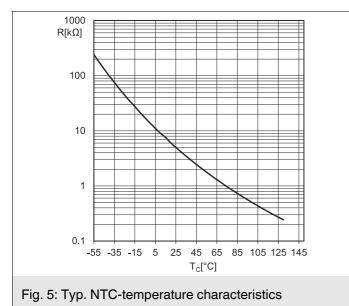
Characteristics							
Symbol	Conditions	min.	typ.	max.	Unit		
Thyristor							
V _T	$T_j = 130 \ ^{\circ}C$, $I_T = 140 \ A$, chiplevel		1.10	1.17	V		
V _{T(TO)}	T _j = 130 °C, chiplevel		0.84	0.91	V		
r _T	T _j = 130 °C, chiplevel		1.85	1.87	mΩ		
I _{DD} ;I _{RD}	$T_j = 130 \text{ °C}, V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$			21	mA		
t _{gd}	$T_j = 25 \text{ °C}, I_G = 1 \text{ A}, di_G/dt = 1 \text{ A}/\mu \text{s}$		1		μs		
t _{gr}	V _D = 0.67 * V _{DRM}		2		μs		
tq	T _j = 130 °C		150		μs		
I _H	$T_j = 25 \ ^{\circ}C$		150	220	mA		
IL	$T_j = 25 \ ^\circ C, R_G = 33 \ \Omega$		300	550	mA		
V _{GT}	$T_j = 25 ^{\circ}C, d.c.$	1.65			V		
I _{GT}	$T_{j} = 25 \ ^{\circ}C, \ d.c.$	100			mA		
V _{GD}	T _j = 130 °C, d.c.			0.25	V		
I _{GD}	$T_j = 130 \ ^{\circ}C, \ d.c.$			3.8	mA		
R _{th(j-c)}	per thyristor, sin. 180°			0.2	K/W		
R _{th(c-s)}	per thyristor (λ_{grease} =0.81 W/(m*K))		0.072		K/W		
R _{th(c-s)}	per thyristor, pre-applied phase change material		0.053		K/W		

Characte	eristics					
Symbol	Conditions		min.	typ.	max.	Unit
Diode						
V _F	I _F = 140 A	T _j = 25 °C		1.04	1.28	V
	chiplevel	T _j = 150 °C		0.95	1.19	V
V _(TO)	chiplevel	T _j = 25 °C		0.88	0.98	V
		T _j = 125 °C		0.73	0.83	V
r _T	chiplevel	T _j = 25 °C		1.13	2.2	mΩ
	chipievei	T _j = 125 °C		1.60	2.5	mΩ
I _{RD}	T _i = 130 °C, V _{RD} = V _{RRM}				2	mA
R _{th(j-c)}	per diode, sin. 180°				0.22	K/W
R _{th(c-s)}	per Diode (λ _{grease} =0.81 W/(m*K))			0.072		K/W
R _{th(c-s)}	per Diode, pre-applied phase change material			0.053		K/W

Characte	eristics					
Symbol	Conditions		min.	typ.	max.	Unit
Module						
L _{CE}				20		nH
$R_{CC'+EE'}$	measured per	T _C = 25 °C		0.8		mΩ
	switch	T _C = 125 °C		1.1		mΩ
Rth _{(c-s)1}	calculated without thermal coupling		0.012			K/W
Rth _{(c-s)2}	including thermal coupling, Ts underneath module (λ_{grease} =0.81 W/ (m*K))			0.020		K/W
Rth _{(c-s)1}	calculated without thermal coupling; pre-applied phase change material			0.009		K/W
Rth _{(c-s)2}	including thermal coupling, Ts underneath module, pre-applied phase change material			0.015		K/W
Ms	to heat sink (M5)		3		6	Nm
M _t	to terminals (M6)		3		6	Nm
w				398		g







300 $I_F[A]$ 250 200 77 150 100 50 T₁ = 25°C $-- - T_{j} = 150^{\circ}C$ 0 0 0.5 1.5 2 1 $V_{F}[V]$

Fig. 2: Diode typ. on-state characteristic, incl. R_{CC'+ EE'}

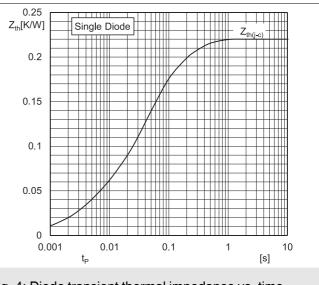
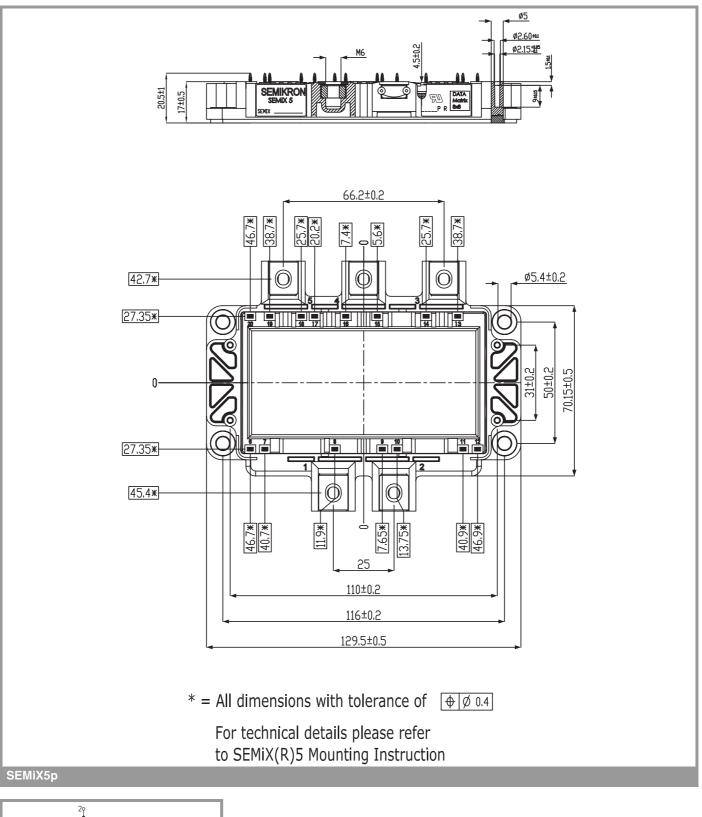
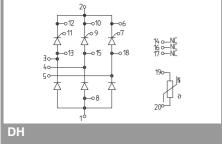


Fig. 4: Diode transient thermal impedance vs. time





This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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